

a second capacitor element connected between said signal input terminal and an input terminal of said second transistor; and

A1  
contd a first impedance element, one end of which is connected to the input terminal of said first transistor, and the other end of which is connected to the input terminal of said second transistor.

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3. (Amended) A semiconductor power amplifier for amplifying a high frequency signal inputted to a signal input terminal by first and second transistors connected in parallel to each other to output the amplified signal via a signal output terminal, said semiconductor power amplifier comprising:

A2 a first capacitor element connected between said signal input terminal and an input terminal of said first transistor;

a second capacitor element connected between said signal input terminal and an input terminal of said second transistor; and

a first impedance element, one end of which is connected to the input terminal of said first transistor, and the other end of which is connected to the input terminal of said second transistor,

a first power amplifying section comprising said first and second transistors, said first and second capacitor elements, and said first impedance element;

a second power amplifying section disposed separately from said first power amplifying section, said second power amplifying section including said first and second transistors, said first and second capacitor elements, and said first impedance element; and

a second impedance element connected between said first impedance element in said first power amplifying section and said first impedance element in said second power amplifying section,

A2  
contd

wherein the respective input terminals of said first and second power amplifying sections are connected to said signal input terminal via the first and second inductor elements.

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13. (Amended) A multistage monolithic integrated circuit comprising:

a plurality of amplifiers connected in cascade,

A3

wherein a last-stage amplifier of these amplifiers includes a semiconductor power amplifier for amplifying a high frequency signal inputted to a signal input terminal by first and second transistors connected in parallel to each other to output the amplified signal via a signal output terminal, said semiconductor power amplifier comprising:

a first capacitor element connected between said signal input terminal and an input terminal of said first transistor;

a second capacitor element connected between said signal input terminal and an input terminal of said second transistor; and

a first impedance element, one end of which is connected to the input terminal of said first transistor, and the other end of which is connected to the input terminal of said second transistor.

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